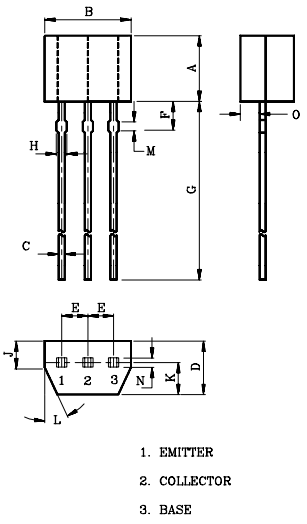
KTA1267L

EPITAXIAL PLANAR PNP TRANSISTOR

LOW NOISE AMPLIFIER APPLICATION.

FEATURES

- Excellent h_{FE} Linearity
  : h_{FE}(0.1mA)/h_{FE}(2mA)=0.95(Typ.).
- Low Noise : NF=0.2dB(Typ.), 3dB(Max.).
- Complementary to KTC3199L.



DIM	MILLIMETERS
A	3.20 MAX
B	4.30 MAX
C	0.55 MAX
D	2.40±0.15
E	1.27
F	2.30
G	14.00±0.50
H	0.60 MAX
J	1.05
K	1.45
L	25°
M	0.80
N	0.55 MAX
O	0.75

1. EMITTER
2. COLLECTOR
3. BASE

TO-92M

MAXIMUM RATINGS (Ta=25℃)

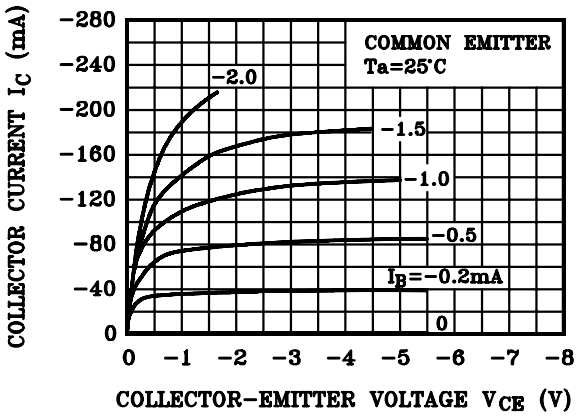
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-150	mA
Emitter Current	I_E	150	mA
Collector Power Dissipation	P_C	400	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55~150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

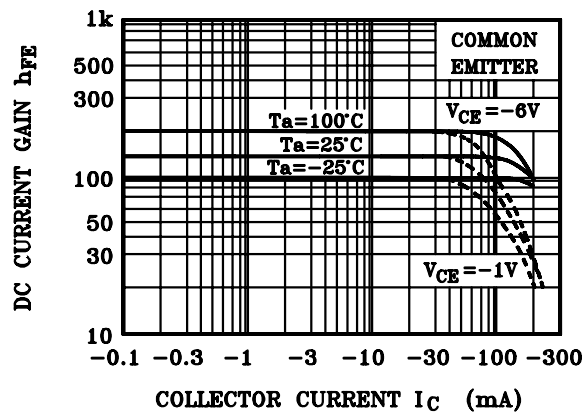
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=-50V, I_E=0	-	-	-0.1	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=-5V, I_C=0	-	-	-0.1	μA
DC Current Gain	h_{FE} (Note)	V_{CE}=-6V, I_C=-2mA	70	-	400	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-100mA, I_B=-10mA	-	-0.1	-0.3	V
Transition Frequency	f_T	V_{CE}=-10V, I_C=-1mA	80	-	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz	-	4.0	7.0	pF
Noise Figure	NF(1)	V_{CE}=-6V, I_C=-0.1mA, f=100Hz, Rg=10kΩ	-	0.5	6.0	dB
	NF(2)	V_{CE}=-6V, I_C=-0.1mA f=1kHz, Rg=10kΩ	-	0.2	3.0	

Note : h_{FE} Classification O:70~140, Y:120~240, GR:200~400

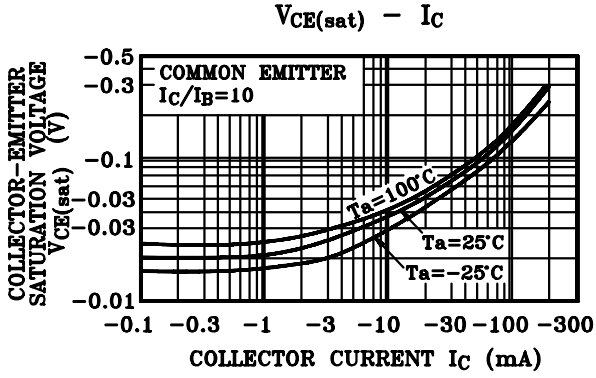
I_C – V_{CE}



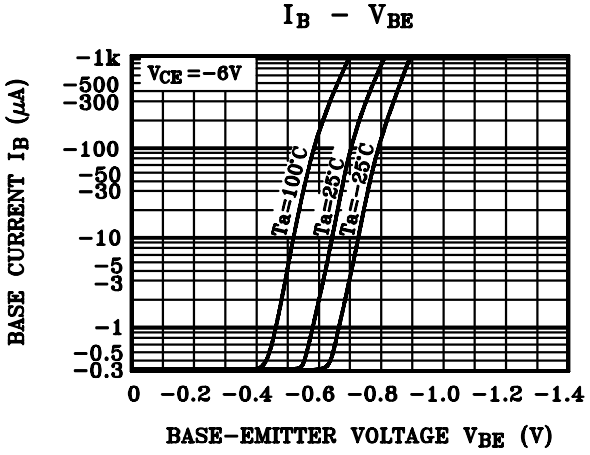
h_{FE} – I_C



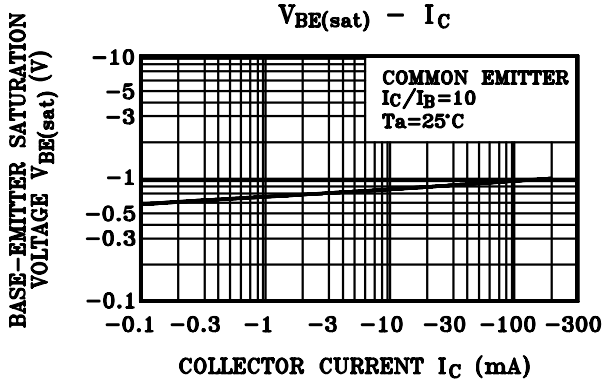
$V_{CE(sat)}$ – I_C



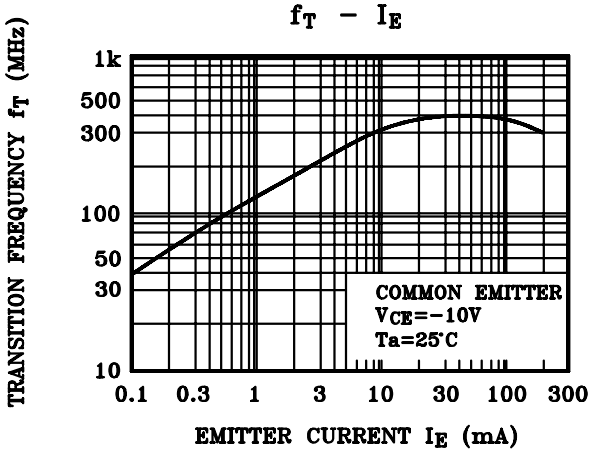
I_B – V_{BE}



$V_{BE(sat)}$ – I_C



f_T – I_E



P_C – Ta

